AMENDMENTS TO THE SPECIFICATION

Please amend the following paragraph beginning at page 10, line 3 as follows.

Fig. 2 (a-c). A scheme of transformation of a silicon whisker, having a solidified globule at its apex, into a silicon tip:

a – an initial stage; b – an intermediate stage; c – a final stage;

1 – silicon substrate; 2 – body of the silicon whisker; 3 – the solidified globule consisting of fine crystallites of silicon and gold; 4 – the tip formed.

Please amend the following paragraph beginning at page 10, line 10 as follows.

Fig. 5 (a-b). A scheme (a) and a scanning-electron-micrograph (b) of a step-shaped silicon tip.

Please amend the following paragraph beginning at page 10, line 17 as follows.

Fig. 8 (a-b). A scheme of a cathode tip structure with multiple-multiple-multiple (M3) field emitters formed by carbon nanotubes on silicon whisker tips;

1 – silicon substrate oriented along the plane (111); 2 – primary silicon whiskers = first link; 3 – secondary silicon whiskers = second link; 4 – nanotubes = third link; 5 – "step" = silicon whisker branching point; 6 – spatial coordinate.

Please amend the following paragraph beginning at page 11, line 9 as follows.

Fig. 13 (a-b). Prior art of the capacitance probes.

a – from [9]: a scheme of the probe, and a scheme of the measurements;

1 – probe, 2 – insulator (oxide), 3 – impurity;

b – from [10]: a scheme of the probe, and a scheme of the measurements;

1 – probe, 2 – oxide.

Please amend the following paragraph beginning at page 11, line 23 as follows.

Fig. 17 (a-b). A scheme of the globule formed on the apex of the silicon whisker.

a – the globule is formed by a mixture of silicon and gold crystallites;

1 – whisker; 2 – silicon crystallite; 3 – gold crystallite;

b – the globule is formed by a mixture of crystallites of silicon, gold, and a third chemical element; 1 – whisker; 2 – silicon crystallite; 3 – gold crystallite; 4 – crystallite of the third chemical element.

Please amend the following paragraph beginning at page 12, line 21 as follows.

Fig. 23 (a-c)~~a, b, c~~. Multilever for scanning probe devices

1 – electrodes of suppression of non-resonance, of deflections indicator and forced deflection system; 2 – silicon lever oriented along the silicon plane (111); 3 – electrode for modulation of the resonant level oscillations; 4, 5 – non-conducting layers; 6 – probe.